

1/6

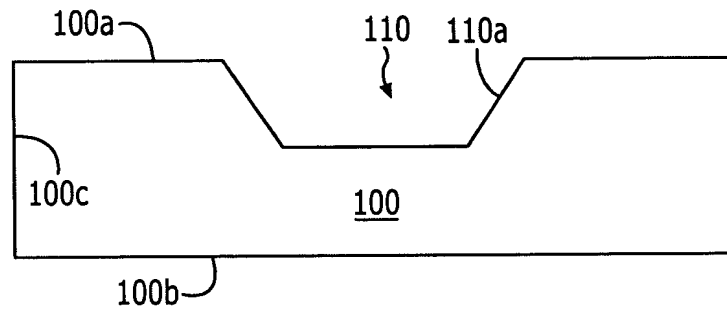


FIG. 1A

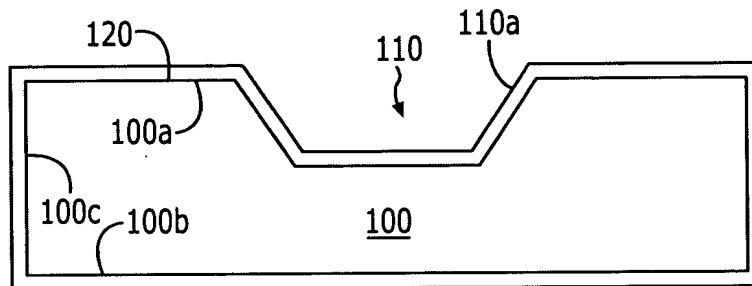


FIG. 1B

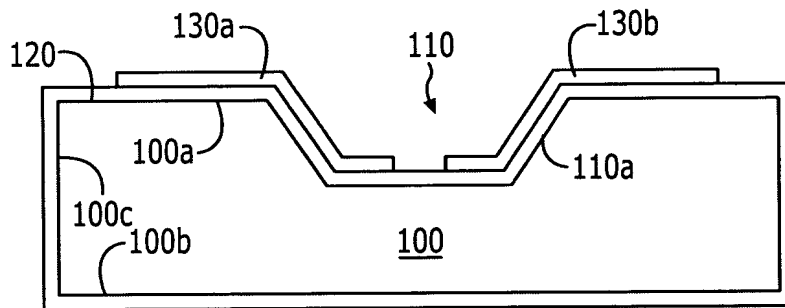


FIG. 1C

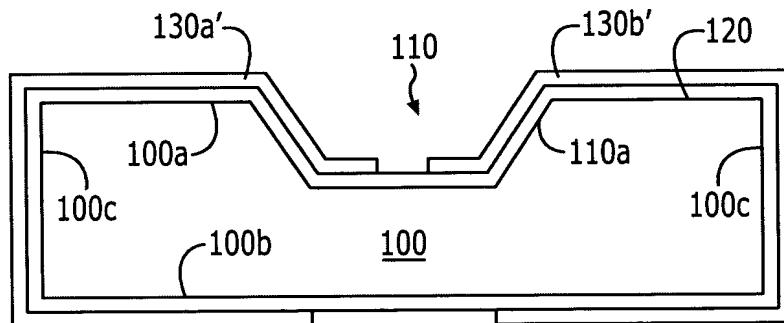


FIG. 1D

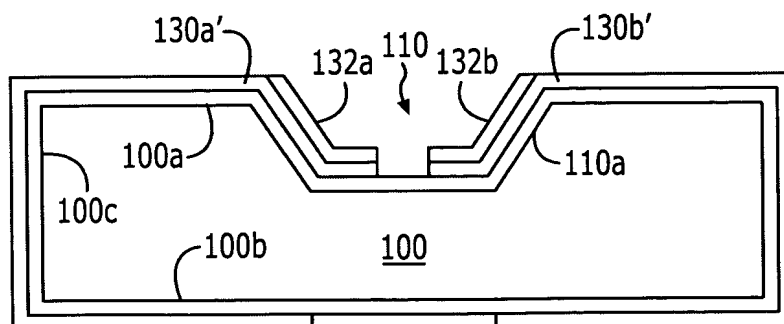
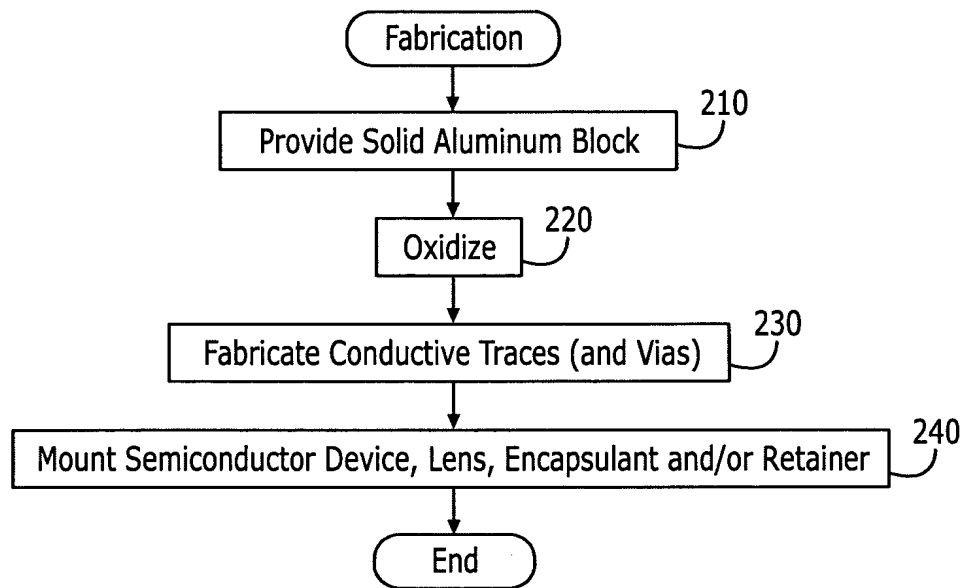


FIG. 1E

**FIG. 1G**

A cross-sectional view of a semiconductor device 110. The device features a central circular region 160, which is a well or cavity, surrounded by a ring-like structure 170. This structure is formed on a substrate 100, which includes a central region 150 and side regions 100a, 100b, and 100c. The device is further defined by a top layer 120 and a bottom layer 130a' and 130b'. The central region 150 is connected to the side regions 100a and 100b by a narrow channel 110a. The side regions 100a and 100b are separated by a narrow gap 100c. The top layer 120 is connected to the side regions 100a and 100b by a narrow channel 180. The bottom layer 130a' and 130b' are connected to the side regions 100a and 100b by a narrow channel 180.

**FIG. 1H**

FIG. 2

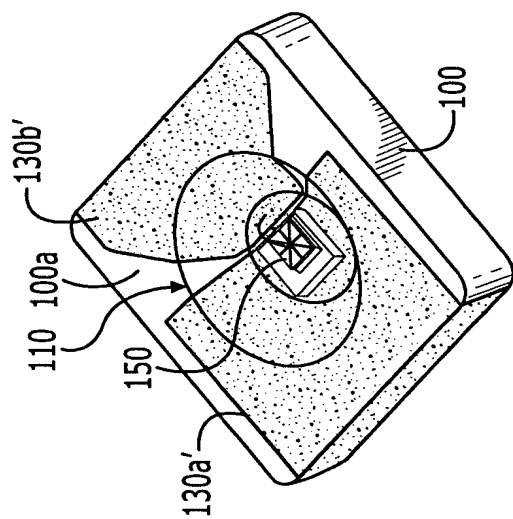


FIG. 3A

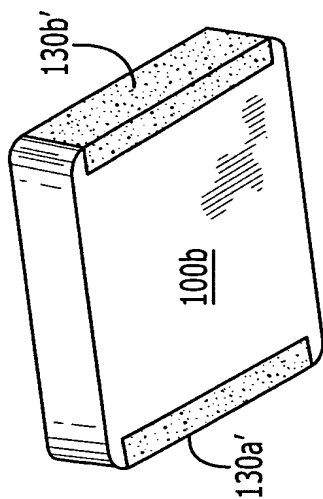
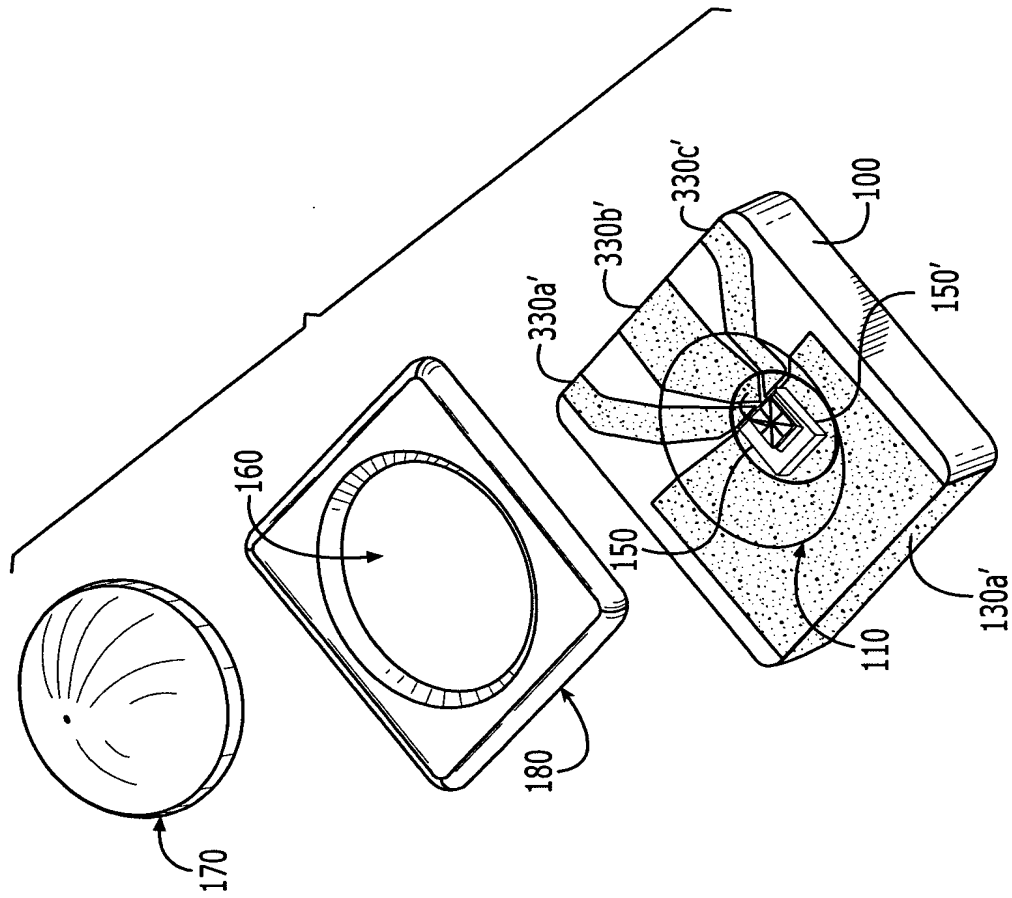


FIG. 3B



**FIG. 4**

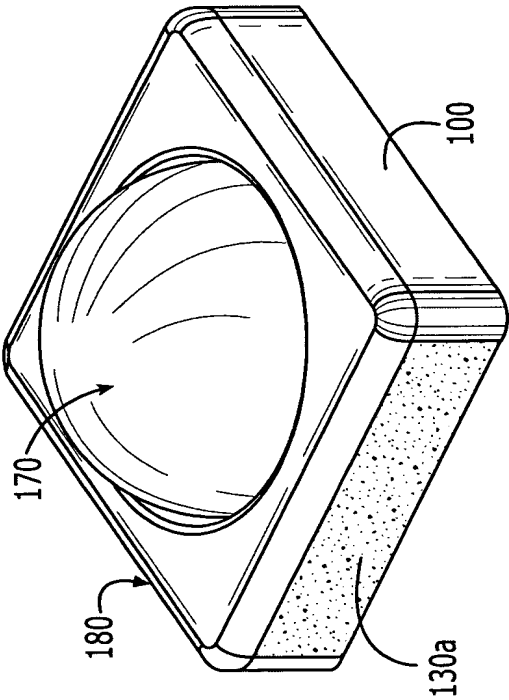


FIG. 5